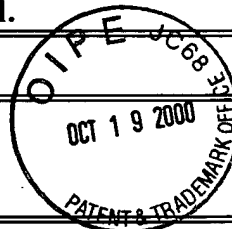


#3

INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 001155	Serial No. 09/660,439
	Applicants: Toshiyuki TAKEMORI et al.	
	Filing Date: September 12, 2000	



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Examiner Initial		Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
<i>SM</i>	AA	4,767,722	Blanchard	8/30/88			
	AB						
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	AD						
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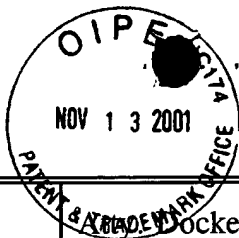
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<i>SM</i>	AF	8-23092	1/23/96	JAPAN	Abstract
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<i>SM</i>	AK	Daisuke Ueda et al., "An Ultra-Low On-Resistance Power MOSFET Fabricated by Using a Fully Self-Aligned Process" IEEE Transaction on Electron Devices, Vol. ED-34, No. 4, April 1987, pp926-930.
<i>SM</i>	AL	D. Kinzer et al., "Ultra-Low Rdson 12 v P-channel trench MOSFET", The 11th International Symposium in Power Semiconductor Devices and Ics, May 26-28, 1999, pp303-306.
Examiner	Date Considered 04/01/2002	



#5

**INFORMATION
DISCLOSURE
CITATION
PTO-1449**

Docket No. 001155

Serial No. 09/660,439

Applicants: Toshiyuki TAKEMORI et al.

Filing Date: September 12, 2000

Group Art Unit: 2812

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Examiner Initial		Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)
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Examiner		Date Considered 04/01/2002